MGBR20L100 Preliminary

MOS GATED BARRIER RECTIFIER

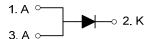
■ DESCRIPTION

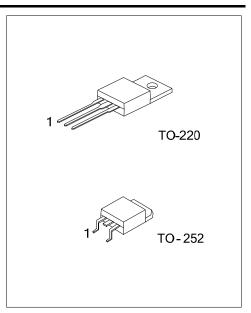
The UTC **MGBR20L100** is a surface mount mos gatedbarrier rectifier,it uses UTC's advanced technology to provide customers withlow forward voltage drop and high switching speed, etc.

■ FEATURES

- * Low forward voltage drop
- * High switching speed

■ SYMBOL



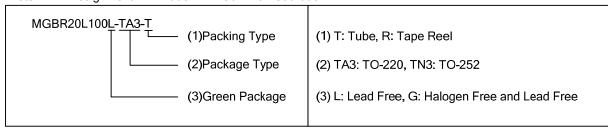


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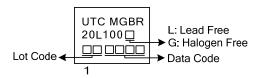
■ ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR20L100L-TA3-T	MGBR20L100G-TA3-T	TO-220	Α	K	Α	Tube	
MGBR20L100L-TN3-R	MGBR20L100G-TN3-R	TO-252	Α	K	Α	Tape Reel	

Note: Pin Assignment: A: Anode K: Common Cathode



■ MARKING



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■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER		SYMBOL	RATINGS	UNIT
DC Blocking Voltage	V_{RM}	100	V	
Working Peak Reverse Voltage	V_{RWM}	100	V	
Repetitive Peak Reverse Voltage	V_{RRM}	100	V	
RMS Reverse Voltage		$V_{R(RMS)}$	80	V
Average Rectified Output Current	T _C =140°C	Ιο	20	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I _{FSM}	250	Α
Operating Junction Temperature		T_J	-65~+150	°C
Storage Temperature		T_{STG}	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS (Note 3)

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	65	°C/W
Junction to Case	$\theta_{ m JC}$	1.4	°C/W

■ **ELECTRICAL CHARACTERISTICS**(T_A=25°C,unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I _R =0.5mA	100			V
Forward Voltage Dran	V _{FM}	I _F =20A, T _J =25°C			0.80	V
Forward Voltage Drop		I _F =20A, T _J =125°C			0.75	V
Lookage Current (Note 1)		V _R =100V, T _J =25°C			300	μΑ
Leakage Current (Note 1)	IRM	V _P =100V, T _I =125°C			30	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.

- 2. Thermal resistance junction to case mounted on heatsink.
- 3. Mounted on an FR4 PCB, single-sided copper, with 100 cm² copper pad area.

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